

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: Not yet assigned
Applicants: Eri TSUKADA, et al.
Filed Internationally: January 19, 2005
US National: Herewith
Title: METHOD FOR PRODUCING SILICON NITRIDE FILMS AND
SILICON OXYNITRIDE FILMS BY CHEMICAL VAPOR
DEPOSITION
TC/A.U: Unknown
Examiner: Unknown
Docket No.: Serie 6497
Customer No.: 000040582

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Prior to an examination of the merits of the above-identified U.S. patent application under 37 C.F.R. § 1.115, please first amend the application as follows:

Amendments to the Claims begin on page 2 of this paper.

Remarks begin on page 4 of this paper.

An **Appendix** including the Abstract is attached following page 4 of this paper.